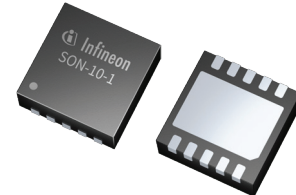


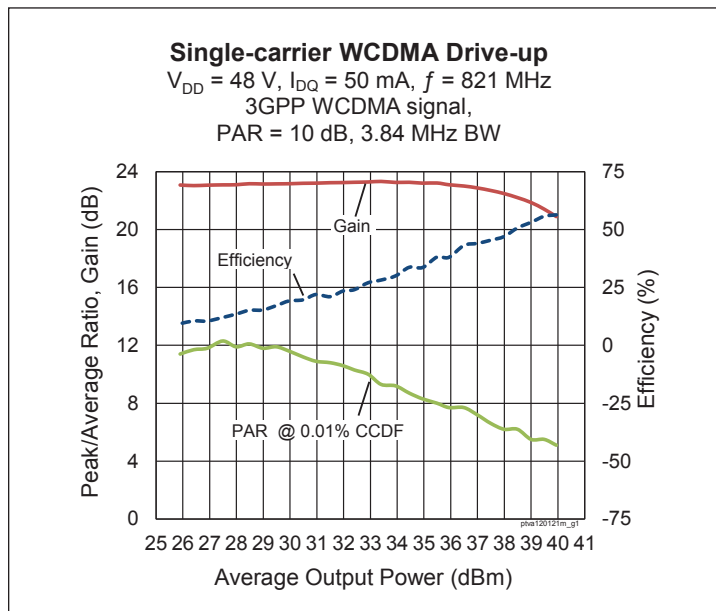
Thermally-Enhanced High Power RF LDMOS FET 12 W, 50 V, 500 – 1400 MHz

Description

The PTVA120121M LDMOS FET is a 12-watt LDMOS FET designed for use in power amplifier applications in the 500 MHz to 1400 MHz frequency band. Features include high gain and a thermally-enhanced, surface-mount package. Manufactured with Infineon's advanced LDMOS process, this device provides excellent thermal performance and superior reliability.



PTVA120121M
Package PG-SON-10



Features

- Unmatched
- Target pulsed CW performance at 821 MHz, 48 V
 - Output power = 12 W P_{1dB}
 - Efficiency = 62%
 - Gain = 22 dB
- Capable of withstanding a 10:1 load mismatch at 50 V, 12 W (CW) output power
- Integrated ESD protection
- Human Body Model class 1B (per ANSI/ESDA/JEDEC JS-001)
- Excellent thermal stability
- Pb-free and RoHS-compliant

RF Characteristics

Single-carrier WCDMA Characteristics (tested in Infineon production test fixture)

$V_{DD} = 48\text{ V}$, $I_{DQ} = 35\text{ mA}$, $P_{OUT} = 3.5\text{ W avg}$, $f = 821\text{ MHz}$, 3GPP WCDMA signal: 3.84 MHz bandwidth, 10 dB PAR @ 0.01% CCDF.

Characteristic	Symbol	Min	Typ	Max	Unit
Gain	G_{ps}	20.5	21.5	—	dB
Drain Efficiency	η_D	35.5	38.5	—	%
Adjacent Channel Power Ratio	ACPR	—	-33.5	-31.5	dBc

All published data at $T_{CASE} = 25^\circ\text{C}$ unless otherwise indicated

ESD: Electrostatic discharge sensitive device—observe handling precautions!

DC Characteristics (each side)

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}$, $I_{DS} = 10\text{ mA}$	$V_{(BR)DSS}$	105	—	—	V
Drain Leakage Current	$V_{DS} = 50\text{ V}$, $V_{GS} = 0\text{ V}$	I_{DSS}	—	—	0.1	μA
	$V_{DS} = 105\text{ V}$, $V_{GS} = 0\text{ V}$	I_{DSS}	—	—	1.0	μA
Gate Leakage Current	$V_{GS} = 10\text{ V}$, $V_{DS} = 0\text{ V}$	I_{GSS}	—	—	0.1	μA
On-State Resistance	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.1\text{ V}$	$R_{DS(on)}$	—	2.96	—	Ω
Operating Gate Voltage	$V_{DS} = 48\text{ V}$, $I_{DQ} = 0.05\text{ A}$	V_{GS}	3	3.57	4	V

Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	105	V
Gate-Source Voltage	V_{GS}	−6 to +12	V
Operating Voltage	V_{DD}	0 to +55	V
Junction Temperature	T_J	225	$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	−65 to +150	$^{\circ}\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance ($T_{CASE} = 70^{\circ}\text{C}$, 13 W CW)	$R_{\theta JC}$	4.9	$^{\circ}\text{C/W}$

Moisture Sensitivity Level

Level	Test Standard	Package Temperature	Unit
3	IPC/JEDEC J-STD-020	260	$^{\circ}\text{C}$

Ordering Information

Type and Version	Order Code	Package Description	Shipping
PTVA120121M V1 R1K	PTVA120121MV1R1KXUMA1	PG-SON-10, molded plastic, SMD	Tape & Reel, 1,000 pcs

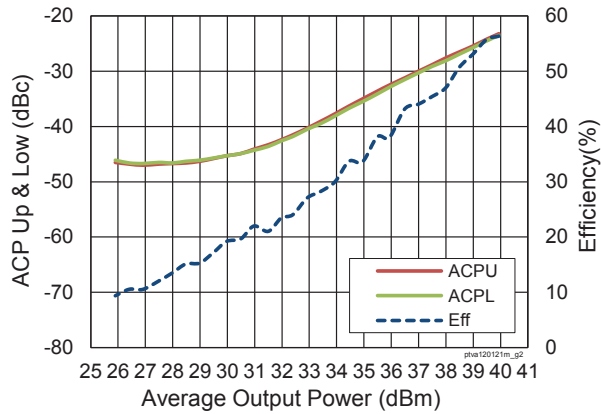
Evaluation Boards

Order Code	Frequency	Description
LTN/PTVA120121M V1	758 – 821 MHz	Class AB, RO4350
LTN/PTVA120121M E2	1200 – 1400 MHz	Class AB, RO3010
LTN/PTVA120121M E3	960 – 1215 MHz	Class AB, RO3010

Typical RF Performance (data taken in production test fixture)

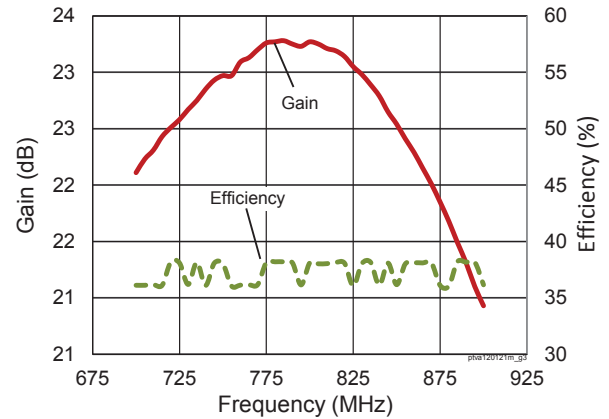
Single-carrier WCDMA Drive-up

$V_{DD} = 48\text{ V}$, $I_{DQ} = 50\text{ mA}$, $f = 821\text{ MHz}$,
 3GPP WCDMA signal, PAR = 10 dB,
 BW = 3.84 MHz



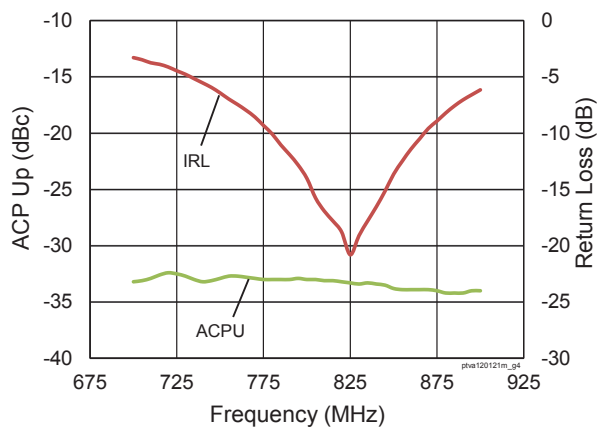
Single-carrier WCDMA Broadband Performance

$V_{DD} = 48\text{ V}$, $I_{DQ} = 50\text{ mA}$, $P_{OUT} = 35.5\text{ dBm}$,
 3GPP WCDMA signal, PAR = 10 dB



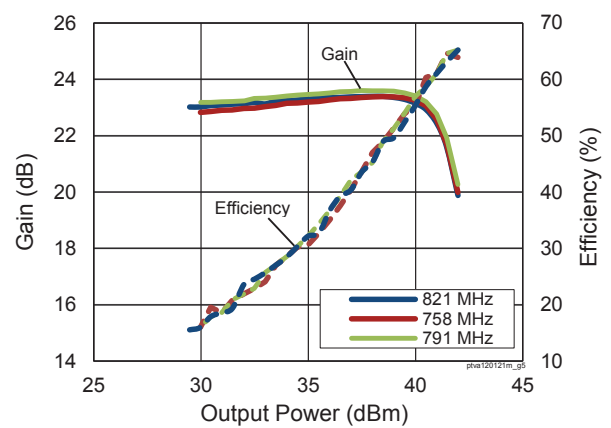
Single-carrier WCDMA Broadband Performance

$V_{DD} = 48\text{ V}$, $I_{DQ} = 50\text{ mA}$, $P_{OUT} = 35.5\text{ dBm}$,
 3GPP WCDMA signal, PAR = 10 dB

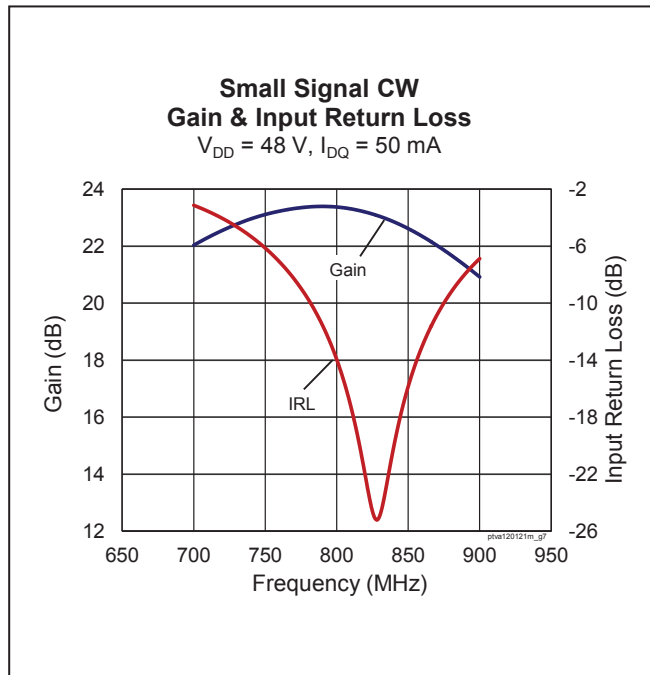
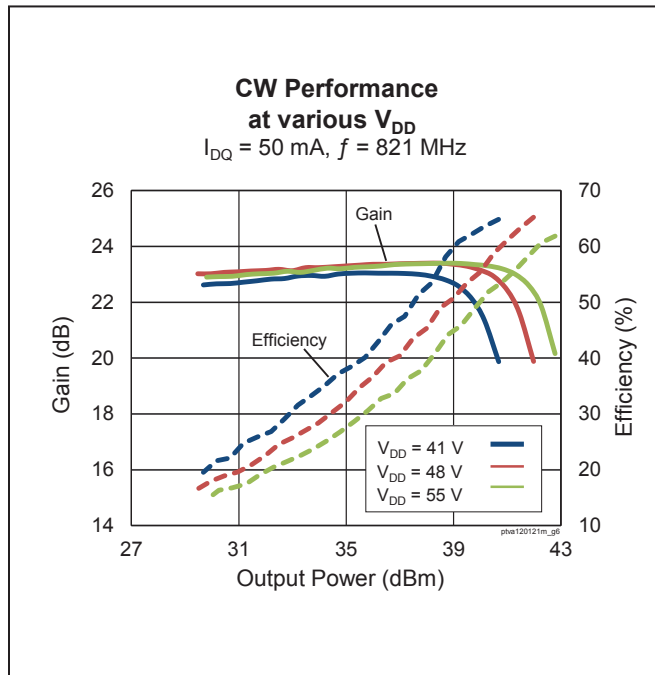


CW Performance

$V_{DD} = 48\text{ V}$, $I_{DQ} = 50\text{ mA}$



Typical RF Performance (cont.)

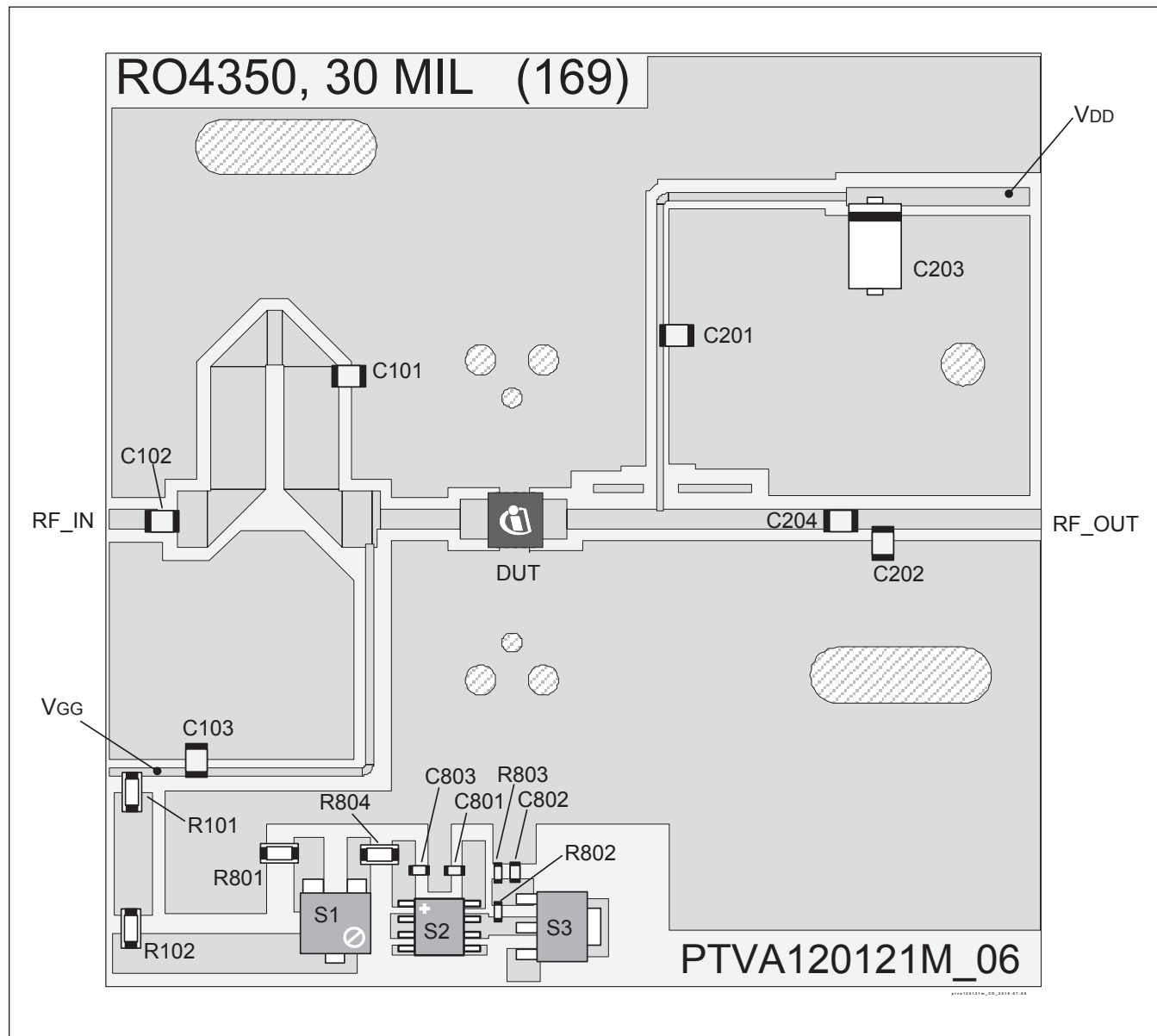


Load Pull Performance

Load Pull Performance – CW signal: 48 V, $I_{DQ} = 36 \text{ mA}$

Freq [MHz]	Z_s [Ω]	Z_l [Ω]	P1dB				Max PAE				
			Max Output Power				Max PAE				
			Gain [dB]	P_{OUT} [dBm]	P_{OUT} [W]	PAE [%]	Z_l [Ω]	Gain [dB]	P_{OUT} [dBm]	P_{OUT} [W]	PAE [%]
758	6.22+j14	44.9+j21.8	22.64	41.69	14.76	66.8	26.9+j64.4	25.3	37.43	5.53	84.0
791	6.07+j12	36.2+j14.5	21.85	42.00	15.93	63.0	23+j62.4	25	36.97	4.97	81.6
821	6.14+j10.9	35+j14.5	21.64	41.94	15.62	63.0	14.8+j50.4	24.9	36.60	4.55	80.2

Reference Circuit, 758 – 821 MHz



Reference circuit assembly diagram (not to scale)

Reference Circuit (cont.)

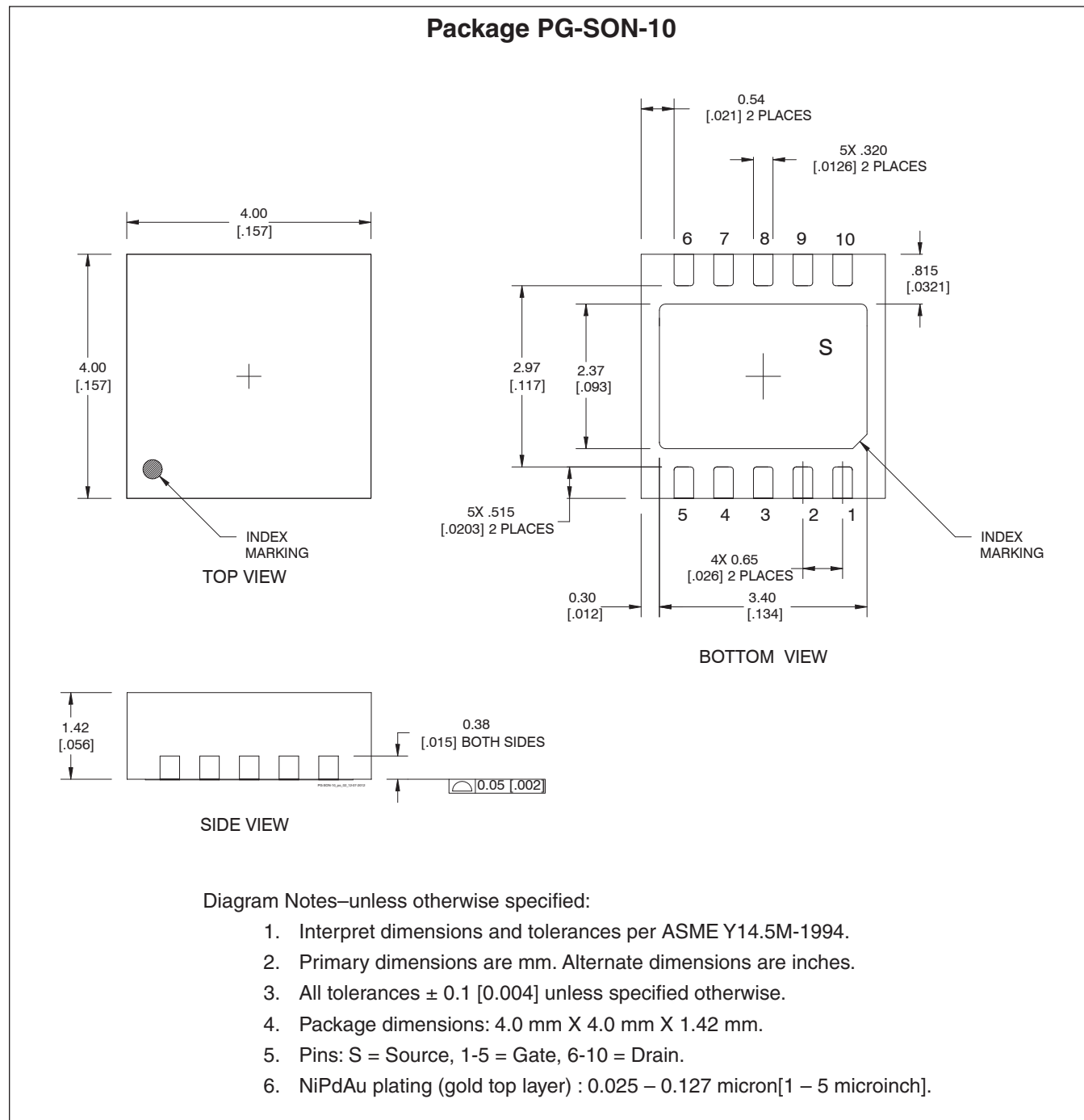
Reference Circuit Assembly

DUT	PTVA120121M V1
Test Fixture Part No.	LTN/PTVA120121M V1
PCB	Rogers 4350, 0.762 mm [0.030"] thick, 2 oz. copper, $\epsilon_r = 3.66$, $f = 758 - 821$ MHz
Find Gerber files for this test fixture on the Infineon Web site at http://www.infineon.com/rfpower	

Components Information

Component	Description	Manufacturer	P/N
Input			
C101	Capacitor, 6.8 pF	ATC	ATC100B6R8CW500XB
C102, C103	Capacitor, 47 pF	ATC	ATC100B470KW500XB
R101	Resistor, 10 ohms	Panasonic Electronic Components	ERJ-8GEYJ100V
R102	Resistor, 200 ohms	Panasonic Electronic Components	ERJ-8GEYJ221V
C801, C802, C803	Capacitor, 1000 pF	Panasonic Electronic Components	ECJ-1VB1H102K
R801	Resistor, 10 ohms	Panasonic Electronic Components	ERJ-8GEYJ100V
R802	Resistor, Chip 1.2K ohms	Panasonic Electronic Components	ERJ-3GEYJ122V
R803	Resistor, Chip 1.3K ohms	Panasonic Electronic Components	ERJ-3GEYJ132V
R804	Resistor, 100 ohms	Panasonic Electronic Components	ERJ-8GEYJ101V
S1	Resistor, Variable 2K ohms	Bourns Inc.	3224W-1-202E
S2	Voltage Regulator	Texas Instruments	LM78L05ACM
S3	Transistor	Infineon Technologies	BCP56
Output			
C201, C204	Capacitor, 47 pF	ATC	ATC100B470KW500XB
C202	Capacitor, 0.9 pF	ATC	ATC100B0R9CW500XB
C203	Capacitor, 10 μ F	AVX / Geratze	TPSE106M050R0400

Package Outline Specifications



Find the latest and most complete information about products and packaging at the Infineon Internet page (www.infineon.com/rtpower)

Revision History

Revision	Date	Data Sheet Type	Page	Subjects (major changes since last revision)
01	2014-10-07	Advance	All	Data Sheet reflects advance specification for product development
02	2016-07-14	Production	All	Data Sheet reflects released product specification
02.1	2017-02-03	Production	2	Update operating voltage and junction temperature

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For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (www.infineon.com/rfpower).

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